



# JCS3205H

## 主要参数 MAIN CHARACTERISTICS

$I_D$	110 A
$V_{DSS}$	55 V
$R_{dson-max}$ (@ $V_{gs}=10V$ )	8 m $\Omega$
$Q_g-typ$	78nC

### 用途

- 高频开关电源
- UPS 电源

### APPLICATIONS

- High efficiency switch mode power supplies
- UPS

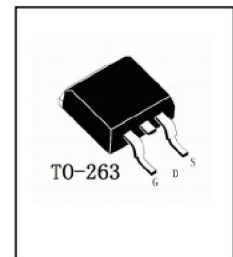
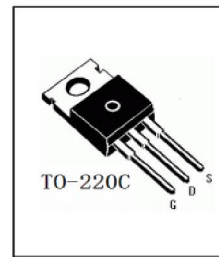
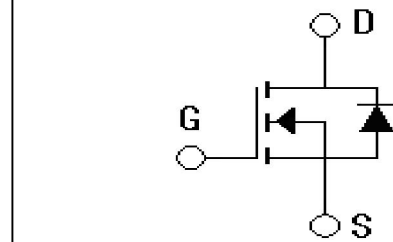
### 产品特性

- 低栅极电荷
- 低  $C_{rss}$  (典型值 197pF)
- 开关速度快
- 产品全部经过雪崩测试
- 高抗  $dv/dt$  能力
- RoHS 产品

### FEATURES

- Low gate charge
- Low  $C_{rss}$  (typical 197pF)
- Fast switching
- 100% avalanche tested
- Improved  $dv/dt$  capability
- RoHS product

## 封装 Package



## 订货信息 ORDER MESSAGE

订货型号 Order codes	印 记 Marking	封 装 Package	无卤素 Halogen Free	包 装 Packaging	器件重量 Device Weight
JCS3205CH-O-C-N-B	JCS3205CH	TO-220C	否 NO	条管 Tube	2.06 g(typ)
JCS3205SH-O-S-N-B	JCS3205SH	TO-263	否 NO	条管 Tube	1.93 g(typ)
JCS3205SH-O-S-N-A	JCS3205SH	TO-263	否 NO	卷盘 Reel	1.93 g(typ)





## 绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最高漏极-源极直流电压 Drain-Source Voltage	$V_{DSS}$	55	V
连续漏极电流 Drain Current -continuous	$I_D$ T=25°C T=100°C	110*	A
		80*	A
最大脉冲漏极电流 (注1) Drain Current – pulse (note 1)	$I_{DM}$	440*	A
最高栅源电压 Gate-Source Voltage	$V_{GSS}$	±20	V
单脉冲雪崩能量 (注2) Single Pulsed Avalanche Energy (note 2)	$E_{AS}$	2970	mJ
雪崩电流 (注1) Avalanche Current (note 1)	$I_{AR}$	60	A
重复雪崩能量 (注1) Repetitive Avalanche Current (note 1)	$E_{AR}$	20	mJ
二极管反向恢复最大电压变化速率 (注3) Peak Diode Recovery dv/dt (note 3)	dv/dt	5.0	V/ns
耗散功率 Power Dissipation	$P_D$ T <sub>C</sub> =25°C -Derate above 25°C	200	W
		1.33	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~+175	°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T <sub>L</sub>	300	°C

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature





## 电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
<b>关态特性 Off –Characteristics</b>						
漏—源击穿电压 Drain-Source Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	55	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$ , referenced to $25^\circ C$	-	0.057	-	V/ $^\circ C$
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=55V, V_{GS}=0V, T_C=25^\circ C$	-	-	1	$\mu A$
		$V_{DS}=44V, T_C=125^\circ C$	-	-	10	$\mu A$
正向栅极体漏电流 Gate-body leakage current, forward	$I_{GSSF}$	$V_{DS}=0V, V_{GS}=20V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	$I_{GSSR}$	$V_{DS}=0V, V_{GS}=-20V$	-	-	-100	nA
<b>通态特性 On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=60A$	-	7	8	m $\Omega$
栅极电阻 Gate Resistance	$R_G$	$f=1.0MHz, \text{open drain}$		1.8		$\Omega$
正向跨导 Forward Transconductance	$g_{fs}$	$V_{DS}=28V, I_D=60A$ (note 4)	-	43	-	S
<b>动态特性 Dynamic Characteristics</b>						
输入电容 Input capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$	-	2750		pF
输出电容 Output capacitance	$C_{oss}$		-	749		pF
反向传输电容 Reverse transfer capacitance	$C_{rss}$		-	197		pF





## 电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	$t_d(\text{on})$	$V_{DD}=28V, I_D=60A, R_G=25\Omega$	-	17	-	ns
上升时间 Turn-On rise time	$t_r$	$V_{GS}=10V$	-	122	-	ns
延迟时间 Turn-Off delay time	$t_d(\text{off})$	(note 4, 5)	-	57	-	ns
下降时间 Turn-Off Fall time	$t_f$		-	72	-	ns
栅极电荷总量 Total Gate Charge	$Q_g$	$V_{DS}=44V,$	-	78	-	nC
栅-源电荷 Gate-Source charge	$Q_{gs}$	$I_D=60A$	-	13.2	-	nC
栅-漏电荷 Gate-Drain charge	$Q_{gd}$	$V_{GS}=10V$ (note 4, 5)	-	37.8	-	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain-Source Diode Forward Current		$I_S$	-	-	110	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		$I_{SM}$	-	-	440	A
正向压降 Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=60A$	-		1.3	V
反向恢复时间 Reverse recovery time	$t_{rr}$	$V_{GS}=0V, I_S=60A$	-	67	127	ns
反向恢复电荷 Reverse recovery charge	$Q_{rr}$	$di_f/dt=100A/\mu s$ (note 4)	-	163	253	nC

## 热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max	单 位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.75	$^{\circ}C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	62.5	$^{\circ}C/W$

注释:

- 1: 脉冲宽度由最高结温限制
- 2:  $L=0.5mH, I_{AS}=60A, V_{DD}=50V, R_G=25\Omega$ , 起始结温  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 60A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$ , 起始结温  $T_J=25^{\circ}C$
- 4: 脉冲测试: 脉冲宽度  $\leq 300\mu s$ , 占空比  $\leq 2\%$
- 5: 基本与工作温度无关

Notes:

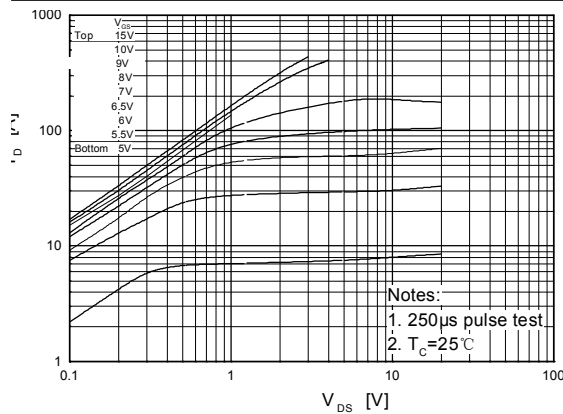
- 1: Pulse width limited by maximum junction temperature
- 2:  $L=0.5mH, I_{AS}=60A, V_{DD}=50V, R_G=25\Omega$ , Starting  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 60A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycles  $\leq 2\%$
- 5: Essentially independent of operating temperature



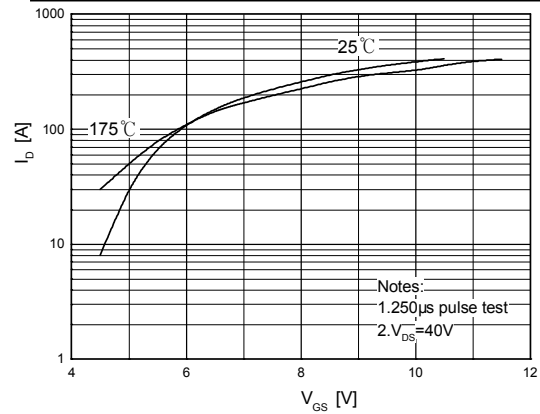


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

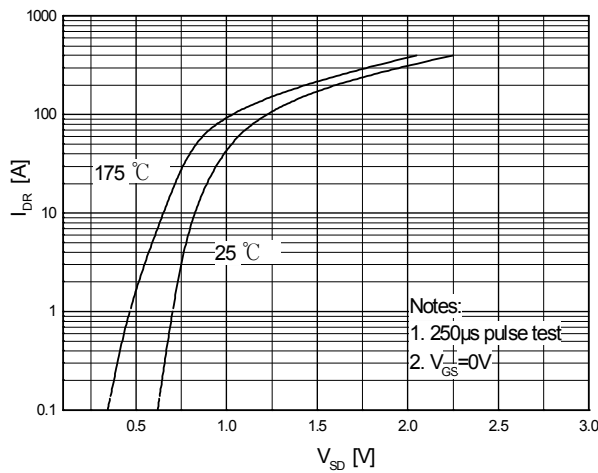
**On-Region Characteristics**



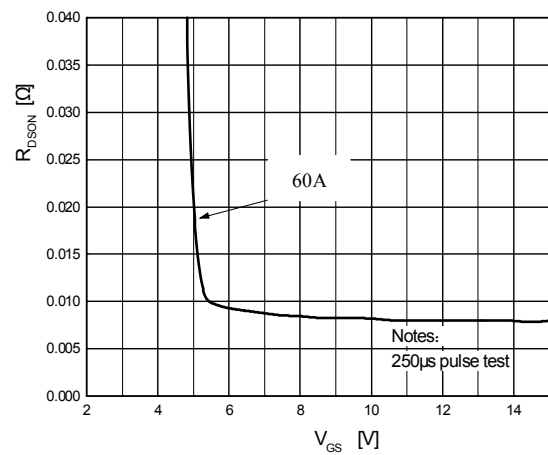
**Transfer Characteristics**



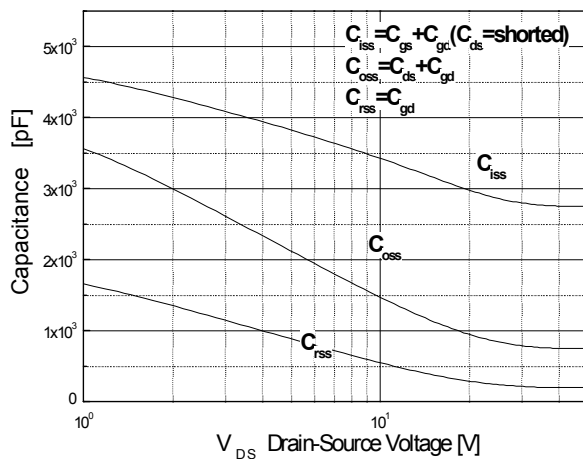
**Body Diode Forward Voltage Variation vs. Source Current and Temperature**



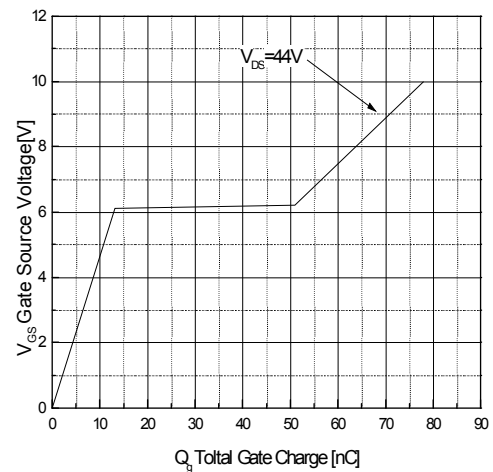
**On-Resistance Variation vs. Drain Current and Gate Voltage**



**Capacitance Characteristics**

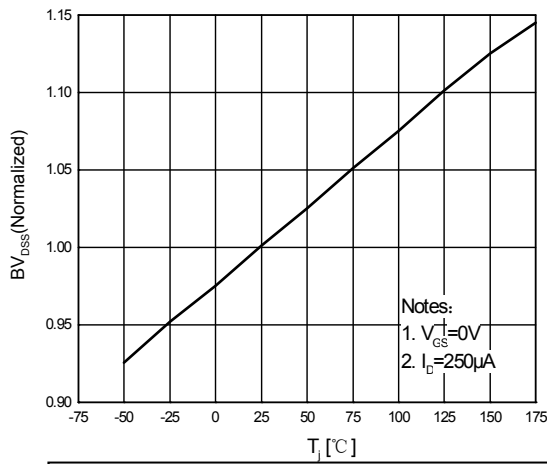


**Gate Charge Characteristics**

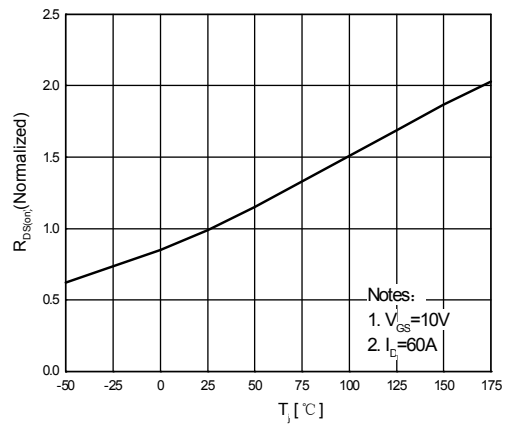


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

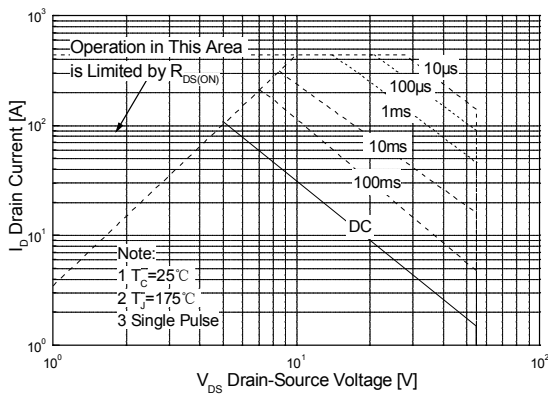
**Breakdown Voltage Variation vs. Temperature**



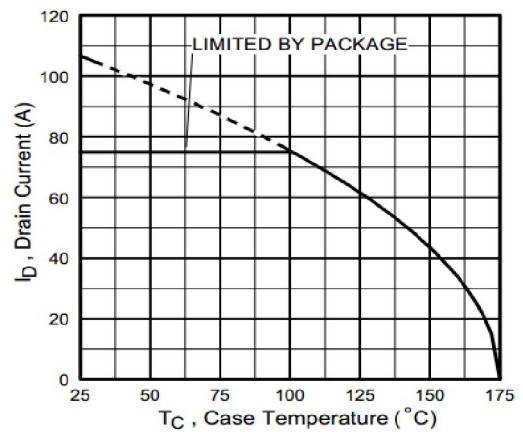
**On-Resistance Variation vs. Temperature**



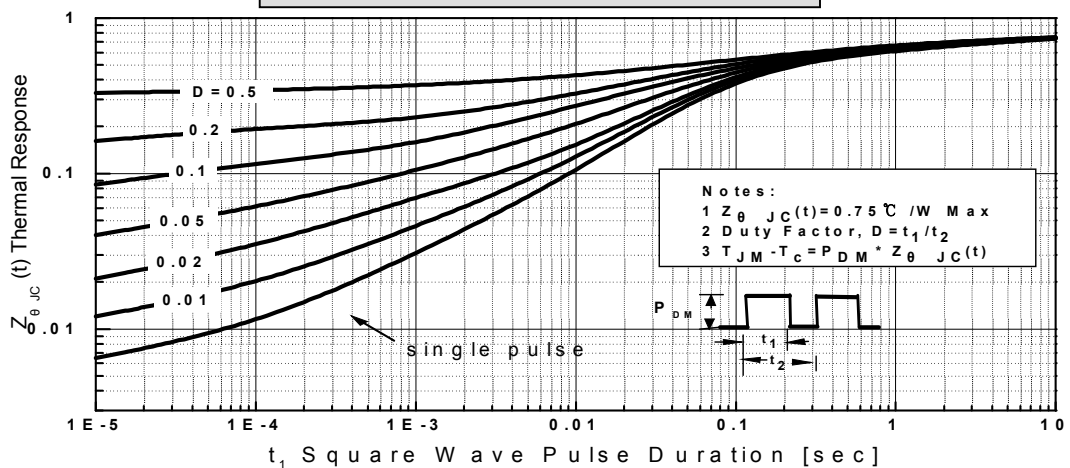
**Maximum Safe Operating Area**



**Maximum Drain Current vs. Case Temperature**



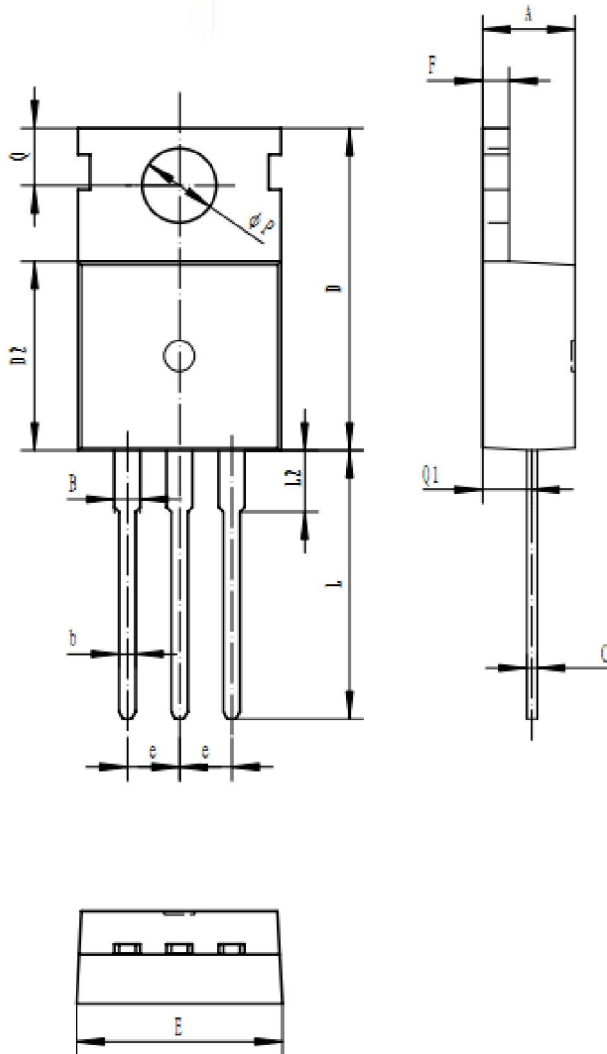
**Transient Thermal Response Curve**



外形尺寸 PACKAGE MECHANICAL DATA

**TO-220C**

单位 Unit: mm

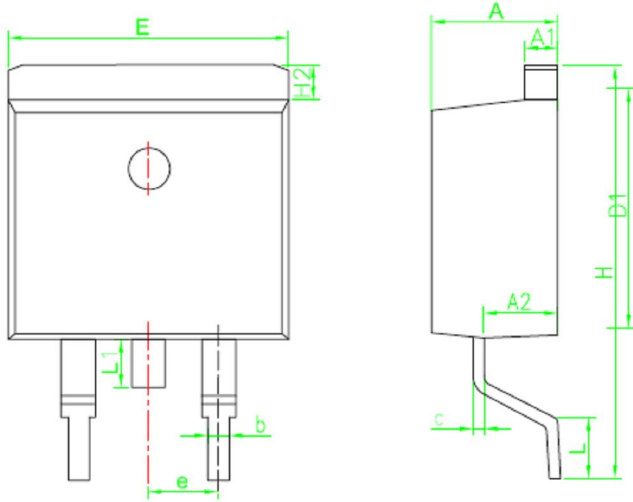


符号 symbol	MIN	MAX
A	4.30	4.70
B	1.22	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80

外形尺寸 PACKAGE MECHANICAL DATA

TO-263

单位 Unit: mm



SYMBOL	MM	
	MIN	MAX
A	4.30	4.80
A1	1.12	1.42
A2	2.54	2.84
b	0.67	1.00
c	0.29	0.52
D1	8.40	9.00
E	9.80	10.46
e	2.54BSC	
H	14.00	16.00
H2	1.12	1.45
L	1.50	3.10
L1	1.45	1.70



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